materials

MDPI

Supplementary Material

Reducing Threading Dislocations of Single-Crystal Diamond via In Situ Tungsten Incorporation

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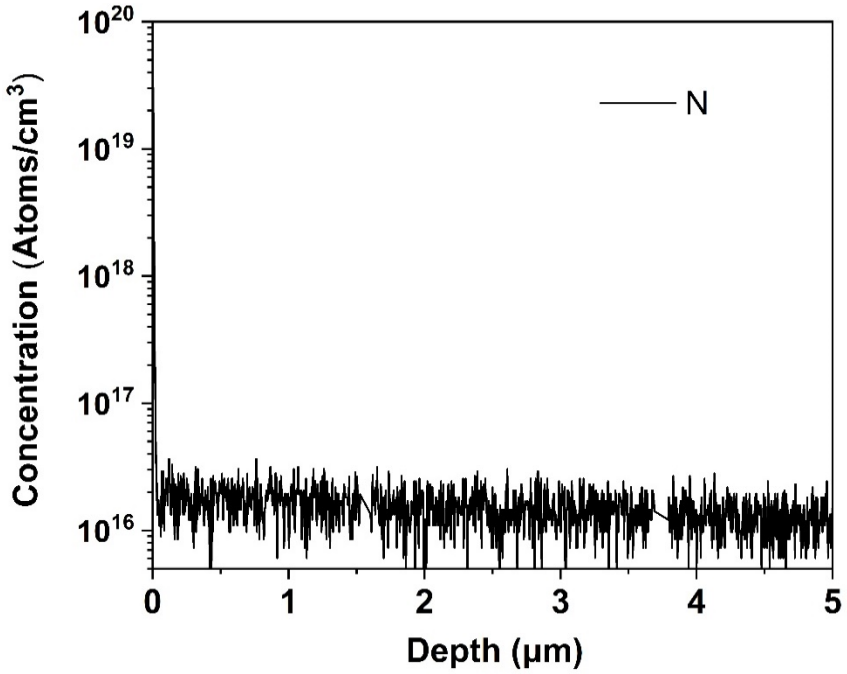


Figure S1. N concentration in TID tested by SIMS.